

## Product Summary

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C
60V	7.5Ω @ V <sub>Gs</sub> = 5V	0.23A

## Features and Benefits

- Dual N-Channel MOSFET
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e.: parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please refer to the related automotive grade (Q-suffix) part. A listing can be found at <https://www.diodes.com/products/automotive/automotive-products/>.**
- **This part is qualified to JEDEC standards (as references in AEC-Q) for High Reliability. <https://www.diodes.com/quality/product-definitions/>**
- **An Automotive-Compliant Part is Available Under Separate Datasheet ([2N7002DWQ](#))**

## Description and Applications

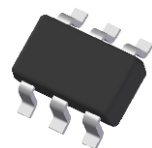
This MOSFET has been designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- Motor Control
- Power Management Functions

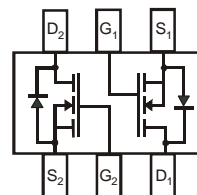
## Mechanical Data

- Case: SOT363
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish Annealed over Alloy 42 Lead-Frame (Lead Free Plating). Solderable per MIL-STD-202, Method 208 (E)
- Terminal Connections: See Diagram
- Weight: 0.006 grams (Approximate)

SOT363 (Standard)



Top View



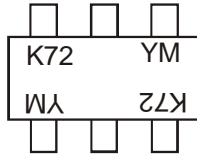
Top View  
Internal Schematic

## Ordering Information (Note 4)

Part Number	Case	Packaging
2N7002DW-7-F	SOT363 (Standard)	3,000/Tape & Reel
2N7002DW-13-F	SOT363 (Standard)	10,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

## Marking Information



K72 = Product Type Marking Code  
 YM = Date Code Marking  
 Y or  $\bar{Y}$  = Year (ex: I = 2021)  
 M or  $\bar{M}$  = Month (ex: 9 = September)

### Date Code Key

Year	2004	...	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	R	...	I	J	K	L	M	N	O	P	R	S

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

## Maximum Ratings (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	$V_{DSS}$	60	V
Drain-Gate Voltage $R_{GS} \leq 1.0M\Omega$	$V_{DGR}$	60	V
Gate-Source Voltage	Continuous	$V_{GSS}$	$\pm 20$
	Pulsed (Note 8)	$V_{GSS}$	$\pm 40$
Continuous Drain Current (Note 6) $V_{GS} = 5V$	Steady State	$T_A = +25^\circ\text{C}$	0.23
		$T_A = +70^\circ\text{C}$	0.18
		$T_A = +100^\circ\text{C}$	0.14
Maximum Continuous Body Diode Forward Current (Note 6)	$I_S$	0.23	A
Pulsed Drain Current (10 $\mu$ s Pulse, Duty Cycle = 1%)	$I_{DM}$	0.8	A

## Thermal Characteristics (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	$P_D$	$T_A = +25^\circ\text{C}$	0.31
		$T_A = +70^\circ\text{C}$	0.2
		$T_A = +100^\circ\text{C}$	0.12
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	410
Total Power Dissipation (Note 6)	$P_D$	$T_A = +25^\circ\text{C}$	0.4
		$T_A = +70^\circ\text{C}$	0.25
		$T_A = +100^\circ\text{C}$	0.15
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	318
Thermal Resistance, Junction to Case (Note 6)	Steady State	$R_{\theta JC}$	135
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 to +150	$^\circ\text{C}$

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
  - Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1inch square copper plate.
  - Short duration pulse test used to minimize self-heating effect.
  - Guaranteed by design. Not subject to product testing.

**Electrical Characteristics** (@  $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 7)</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	60	70	—	V	$V_{GS} = 0V, I_D = 10\mu A$
Zero Gate Voltage Drain Current	$I_{DSS}$	—	—	1.0 500	$\mu A$	$V_{DS} = 60V, V_{GS} = 0V$ @ $T_C = +25^\circ\text{C}$ @ $T_C = +125^\circ\text{C}$
Gate-Body Leakage	$I_{GSS}$	—	—	$\pm 10$	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
<b>ON CHARACTERISTICS (Note 7)</b>						
Gate Threshold Voltage	$V_{GS(TH)}$	1.0	—	2.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	3.2 4.4	7.5 13.5	$\Omega$	$V_{GS} = 5.0V, I_D = 0.05A$ $V_{GS} = 10V, I_D = 0.5A$
On-State Drain Current	$I_{D(ON)}$	0.5	1.0	—	A	$V_{GS} = 10V, V_{DS} = 7.5V$
Forward Transconductance	$g_{FS}$	80	—	—	mS	$V_{DS} = 10V, I_D = 0.2A$
Diode Forward Voltage	$V_{SD}$	—	0.78	1.5	V	$V_{GS} = 0V, I_S = 115mA$
<b>DYNAMIC CHARACTERISTICS (Note 8)</b>						
Input Capacitance	$C_{iss}$	—	22	50	pF	$V_{DS} = 25V, V_{GS} = 0V$ $f = 1.0MHz$
Output Capacitance	$C_{oss}$	—	11	25	pF	
Reverse Transfer Capacitance	$C_{rss}$	—	2.0	5.0	pF	
Turn-On Delay Time	$t_{D(ON)}$	—	7.0	20	ns	$V_{DD} = 30V, I_D = 0.2A,$ $R_L = 150\Omega, V_{GEN} = 10V,$ $R_{GEN} = 25\Omega$
Turn-Off Delay Time	$t_{D(OFF)}$	—	11.0	20		

Notes: 7. Short duration pulse test used to minimize self-heating effect.  
8. Guaranteed by design. Not subject to product testing.

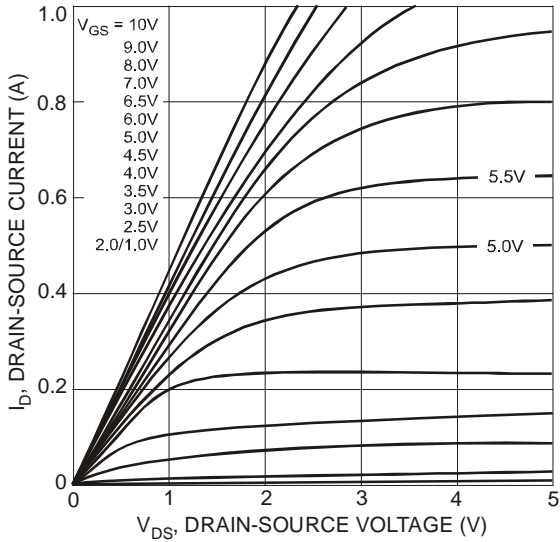


Figure 1 On-Region Characteristics

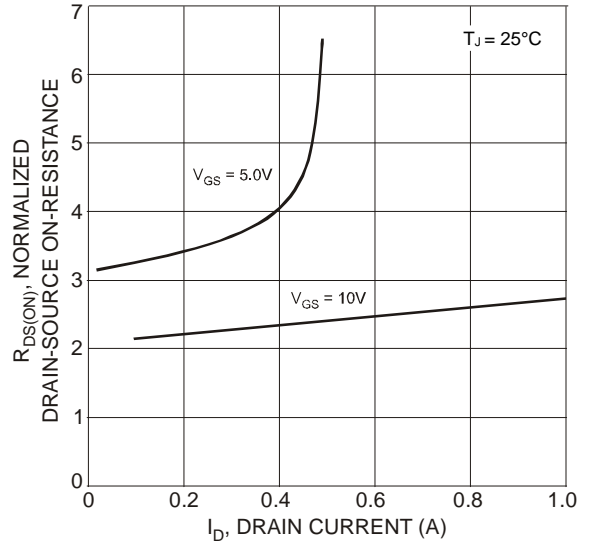


Figure 2 On-Resistance vs. Drain Current

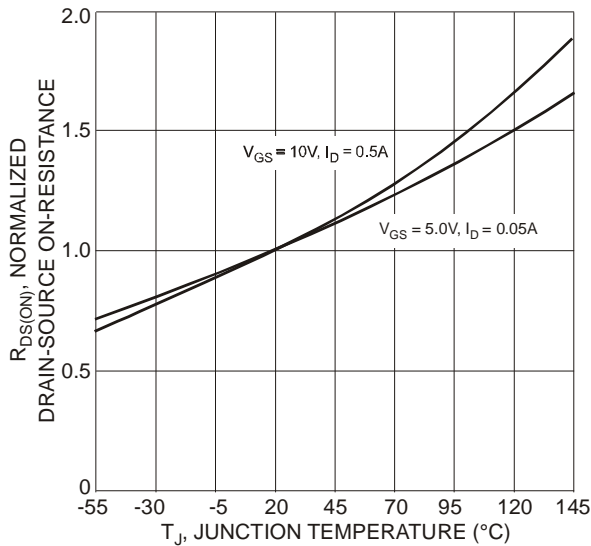


Figure 3 On-Resistance vs. Junction Temperature

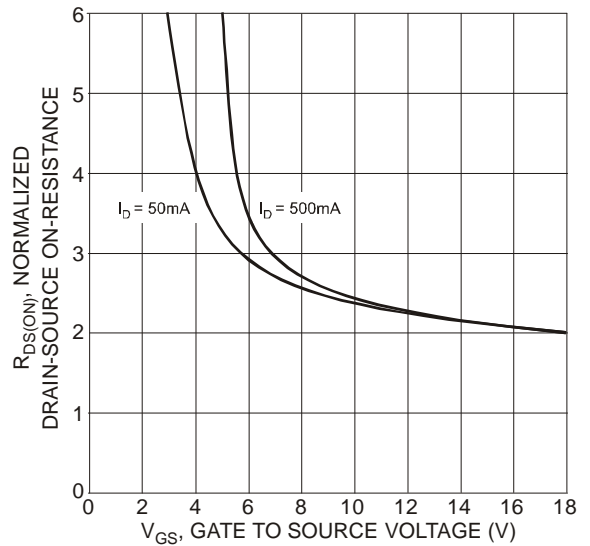


Figure 4 On-Resistance vs. Gate-Source Voltage

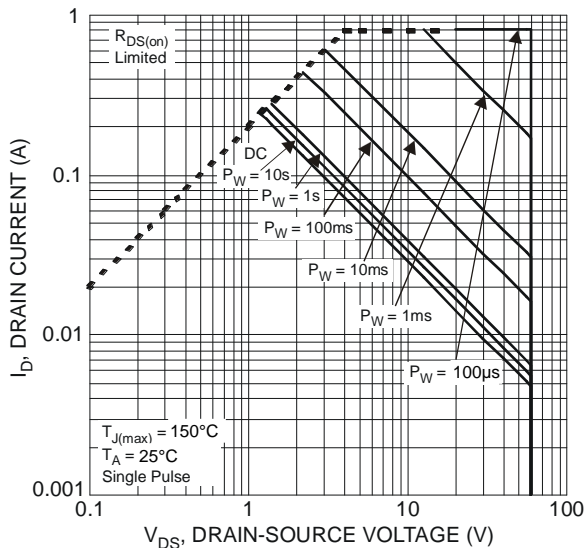
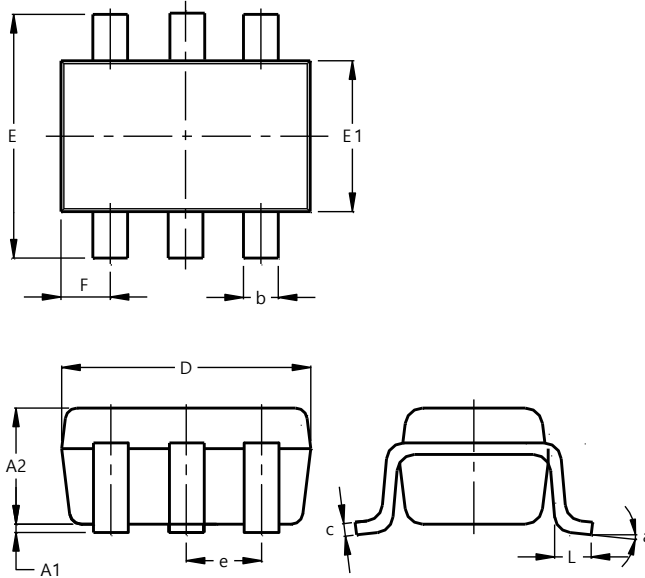


Figure 5 SOA, Safe Operation Area

## Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT363 (Standard)

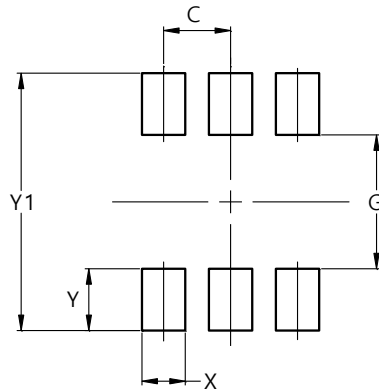


SOT363 (Standard)			
Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.80	1.00	0.90
b	0.10	0.35	0.225
c	0.08	0.22	0.15
D	1.80	2.20	2.00
E	2.00	2.45	2.225
E1	1.15	1.35	1.25
e	--	--	0.65
F	0.25	0.45	0.35
L	0.25	0.46	0.355
a	0°	8°	--
All Dimensions in mm			

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

SOT363 (Standard)



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.420
Y	0.600
Y1	2.500